NLAS4684

Analog Switch, Dual SPDT, Ultra-Low Resistance

The NLAS4684 is an advanced CMOS analog switch fabricated in Sub−micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra−Low R_{ON} of 0.5 Ω, for the Normally Closed (NC) switch, and 0.8 Ω for the Normally Opened switch (NO) at 2.7 V.

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS4684 is available in a 2.0 x 1.5 mm bumped die array. The pitch of the solder bumps is 0.5 mm for easy handling.

Features

- Ultra−Low R_{ON}, < 0.5 Ω at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at V_{CC} = 2.7−3.3 V
- Single Supply Operation from 1.8−5.5 V
- Tiny 2 x 1.5 mm Bumped Die
- Low Crosstalk, < 83 dB at 100 kHz
- Full 0−V_{CC} Signal Handling Capability
- High Isolation, −65 dB at 100 kHz
- Low Standby Current, < 50 nA
- Low Distortion, < 0.14% THD
- R_{ON} Flatness of 0.15 Ω
- Pin for Pin Replacement for MAX4684
- High Continuous Current Capability
  ± 300 mA Through Each Switch
- Large Current Clamping Diodes at Analog Inputs
  ± 300 mA Continuous Current Capability
- Pb−Free Packages are Available

Applications

- Cell Phone
- Speaker Switching
- Power Switching
- Modems
- Automotive

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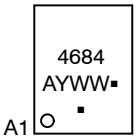
MARKING DIAGRAMS

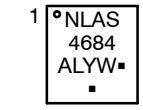
A1

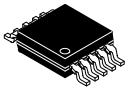
Microbump−10
CASE 489AA



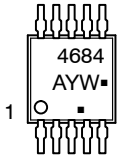
1

DFN10
CASE 485C





Micro10
CASE 846B



A	= Assembly Location
L	= Wafer Lot
Y	= Year
WW, W	= Work Week
▪	= Pb−Free Package

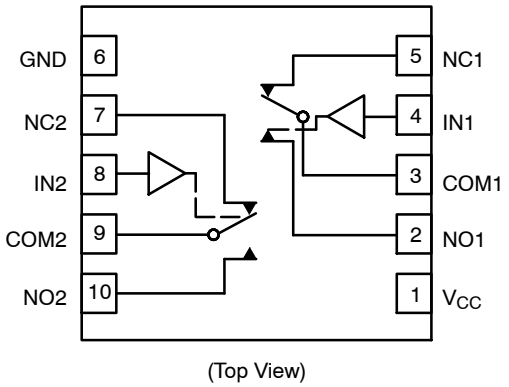
(Note: Microdot may be in either location)

FUNCTION TABLE

IN 1, 2	NO 1, 2	NC 1, 2
0	OFF	ON
1	ON	OFF

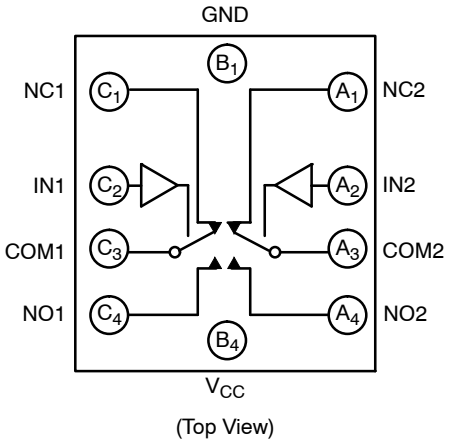
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.



(Top View)

Figure 1. Pin Connections and Logic Diagram (DFN10 and Micro10)



(Top View)

Figure 2. Pin Connections and Logic Diagram (Microbump−10)

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Positive DC Supply Voltage	−0.5 to +7.0	V
V_{IS}	Analog Input Voltage (V_{NO}, V_{NC}, or V_{COM})	$-0.5 \le V_{IS} \le V_{CC} + 0.5$	V
V_{IN}	Digital Select Input Voltage	$-0.5 \le V_I \le +7.0$	V
I_{anl1}	Continuous DC Current from COM to NC/NO	±300	mA
$I_{anl-pk\ 1}$	Peak Current from COM to NC/NO, 10 duty cycle (Note 1)	±500	mA
I_{clmp}	Continuous DC Current into COM/NO/NC	±300	mA
$I_{clmp\ 1}$	Peak Current into Input Clamp Diodes at COM/NC/NO	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Defined as 10% ON, 90% off duty cycle.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		1.8	5.5	V
V_{IN}	Digital Select Input Voltage		GND	5.5	V
V_{IS}	Analog Input Voltage (NC, NO, COM)		GND	V_{CC}	V
T_A	Operating Temperature Range		−55	+125	°C
t_r, t_f	Input Rise or Fall Time, SELECT	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V
ESD	Human Body Model − All Pins			5	kV

DC CHARACTERISTICS − Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} ±10%	Guaranteed Limit			Unit
				−55°C to 25°C	<85°C	<125°C	
V_{IH}	Minimum High−Level Input Voltage, Select Inputs (Figure 9)		2.0 2.5 3.0 5.0	1.4 1.4 1.4 2.0	1.4 1.4 1.4 2.0	1.4 1.4 1.4 2.0	V
V_{IL}	Maximum Low−Level Input Voltage, Select Inputs (Figure 9)		2.0 2.5 3.0 5.0	0.5 0.5 0.5 0.8	0.5 0.5 0.5 0.8	0.5 0.5 0.5 0.8	V
I_{IN}	Maximum Input Leakage Current, Select Inputs	V_{IN} = 5.5 V or GND	5.5	± 1.0	± 1.0	± 1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or GND	0	±10	±10	±10	μA
I_{CC}	Maximum Quiescent Supply Current (Note 2)	Select and V_{IS} = V_{CC} or GND	5.5	± 180	± 200	± 200	nA

2. Guaranteed by design.

DC ELECTRICAL CHARACTERISTICS – Analog Section

Symbol	Parameter	Condition	V_{CC} ±10%	Guaranteed Maximum Limit						Unit
				–55°C to 25°C		<85°C		<125°C		
				Min	Max	Min	Max	Min	Max	
R_{ON} (NC)	NC "ON" Resistance (Note 3)	$V_{IN} \le V_{IL}$ V_{IS} = GND to V_{CC} $I_{IN}I \le 100$ mA	2.5 3.0 5.0		0.6 0.5 0.4		0.7 0.5 0.4		0.8 0.5 0.5	Ω
R_{ON} (NO)	NO "ON" Resistance (Note 3)	$V_{IN} \ge V_{IH}$ V_{IS} = GND to V_{CC} $I_{IN}I \le 100$ mA	2.5 3.0 5.0		1.0 0.8 0.8		1.0 0.8 0.8		1.0 1.0 0.9	Ω
$R_{FLAT\ (NC)}$	NC_On–Resistance Flatness (Notes 3, 5)	I_{COM} = 100 mA V_{IS} = 0 to V_{CC}	2.5 3.0 5.0		0.15 0.15 0.15		0.15 0.15 0.15		0.15 0.15 0.15	Ω
$R_{FLAT\ (NO)}$	NO_On–Resistance Flatness (Notes 3, 5)	I_{COM} = 100 mA V_{IS} = 0 to V_{CC}	2.5 3.0 5.0		0.35 0.35 0.35		0.35 0.35 0.35		0.35 0.35 0.35	Ω
ΔR_{ON}	On–Resistance Match Between Channels (Notes 3 and 4)	V_{IS} = 1.3 V; I_{COM} = 100 mA V_{IS} = 1.5 V; I_{COM} = 100 mA V_{IS} = 2.8 V; I_{COM} = 100 mA	2.5 3.0 5.0		0.18 0.06 0.06		0.18 0.06 0.06		0.18 0.06 0.06	Ω
$I_{NC(OFF)}$ $I_{NO(OFF)}$	NC or NO Off Leakage Current (Figure 13) (Note 3)	V_{IN} = V_{IL} or V_{IH} V_{NO} or V_{NC} = 1.0 V_{COM} = 4.5 V	5.5	–1	1	–10	10	–100	100	nA
$I_{COM(ON)}$	COM ON Leakage Current (Figure 13) (Note 3)	V_{IN} = V_{IL} or V_{IH} V_{NO} 1.0 V or 4.5 V with V_{NC} floating or V_{NC} 1.0 V or 4.5 V with V_{NO} floating V_{COM} = 1.0 V or 4.5 V	5.5	–2	2	–20	20	–200	200	nA

3. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
4. $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$ between NC1 and NC2 or between NO1 and NO2.
5. Flatness is defined as the difference between the maximum and minimum value of on–resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns) (Typical characteristics are at 25°C)

Symbol	Parameter	Test Conditions	V_{CC} (V)	V_{IS} (V)	Guaranteed Maximum Limit							Unit
					−55°C to 25°C			<85°C		<125°C		
					Min	Typ	Max	Min	Max	Min	Max	
t_{ON}	Turn−On Time	R_L = 50 Ω, C_L = 35 pF (Figures 4 and 5)	2.5	1.3			60		70		70	ns
			3.0	1.5			50		60		60	
			5.0	2.8			30		35		35	
t_{OFF}	Turn−Off Time	R_L = 50 Ω, C_L = 35 pF (Figures 4 and 5)	2.5	1.3			50		55		55	ns
			3.0	1.5			40		50		50	
			5.0	2.8			30		35		35	
t_{BBM}	Minimum Break−Before−Make Time (Note 6)	V_{IS} = 3.0 R_L = 300 Ω, C_L = 35 pF (Figure 3)	3.0	1.5	2	15						ns

		Typical @ 25, V_{CC} = 5.0 V	
C_{NC} Off	NC Off Capacitance, f = 1 MHz	102	pF
C_{NO} Off	NO Off Capacitance, f = 1 MHz	104	
C_{NC} On	NC On Capacitance, f = 1 MHz	322	
C_{NO} On	NO On Capacitance, f = 1 MHz	330	

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Condition		V_{CC} V	Typical 25°C	Unit
BW	Maximum On−Channel −3dB Bandwidth or Minimum Frequency Response	V_{IN} = 0 dBm	NC	3.0	6.5	MHz
		V_{IN} centered between V_{CC} and GND (Figure 6)	NO	3.0	9.5	
V_{ONL}	Maximum Feed−through On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 6)		3.0	−0.05	dB
V_{ISO}	Off−Channel Isolation (Note 7)	f = 100 kHz; V_{IS} = 1 V RMS; C_L = 5 nF V_{IN} centered between V_{CC} and GND(Figure 6)		3.0	−65	dB
Q	Charge Injection Select Input to Common I/O (Figures 10 and 11)	V_{IN} = $V_{CC\ to}$ GND, R_{IS} = 0 Ω, C_L = 1 nF Q = C_L − ΔV_{OUT} (Figure 7)		3.0	15	pC
THD	Total Harmonic Distortion THD + Noise (Figure 9)	F_{IS} = 20 Hz to 100 kHz, R_L = R_{gen} = 600 Ω, C_L = 50 pF V_{IS} = 1 V RMS		3.0	0.14	%
VCT	Channel−to−Channel Crosstalk	f = 100 kHz; V_{IS} = 1 V RMS, C_L = 5 pF, R_L = 50 Ω V_{IN} centered between V_{CC} and GND (Figure 6)		3.0	−83	dB

6. −55°C specifications are guaranteed by design.
7. Off−Channel Isolation = 20log10 (Vcom/Vno) (See Figure 6).

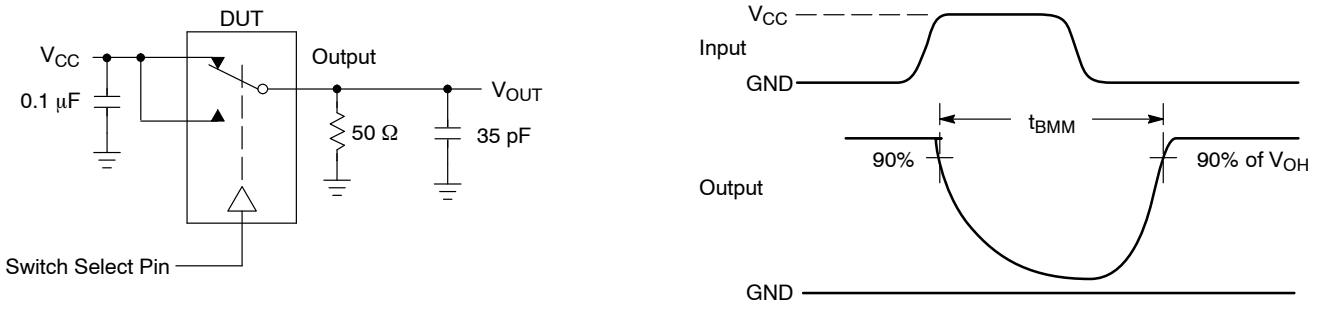


Figure 3. t_{BBM} (Time Break−Before−Make)

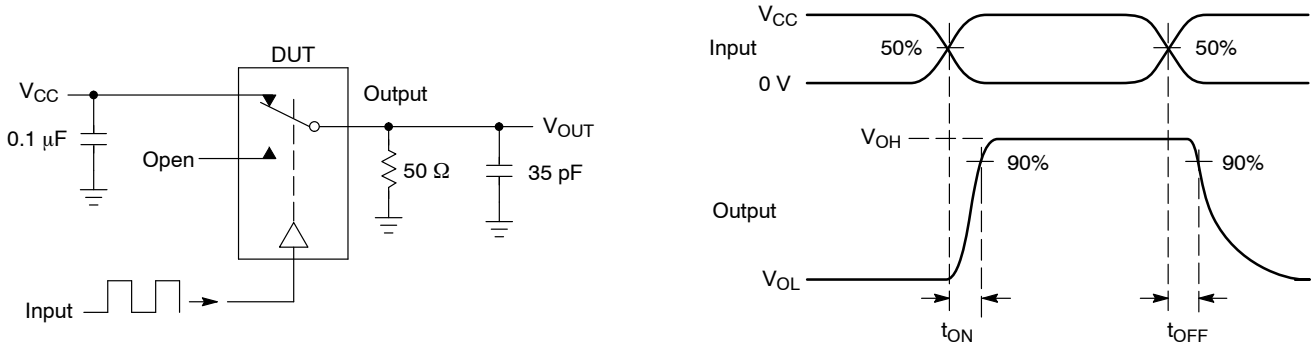


Figure 4. t_{ON}/t_{OFF}

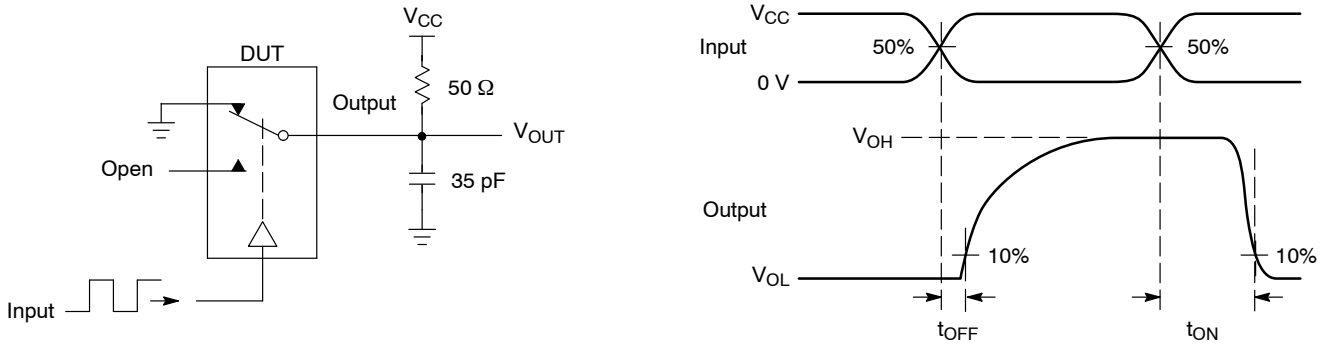
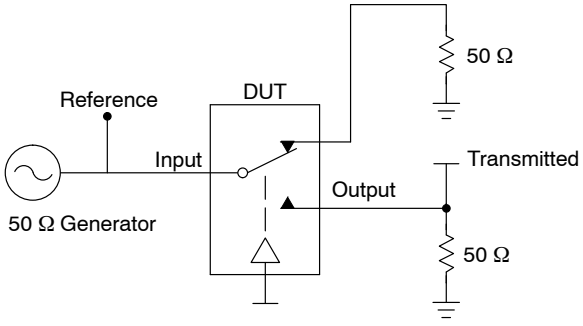


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO}, Bandwidth and V_{ONL} are independent of the input signal direction.

V_{ISO} = Off Channel Isolation = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz

V_{ONL} = On Channel Loss = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}
V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

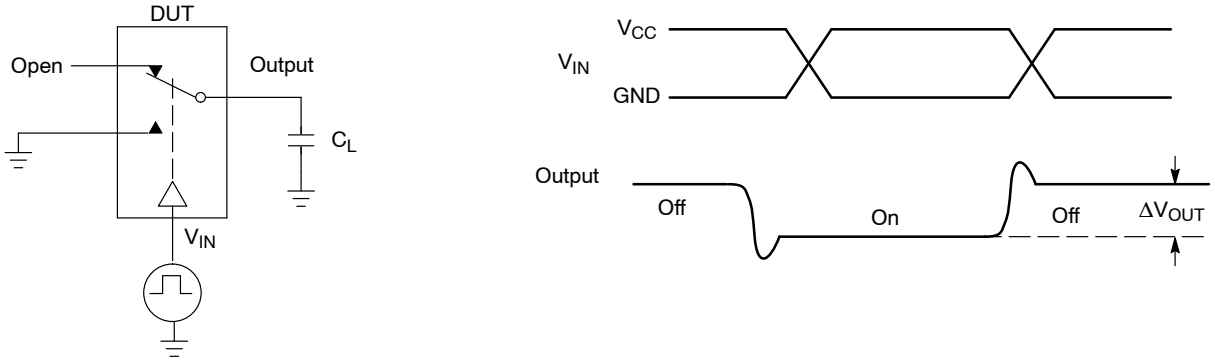


Figure 7. Charge Injection: (Q)

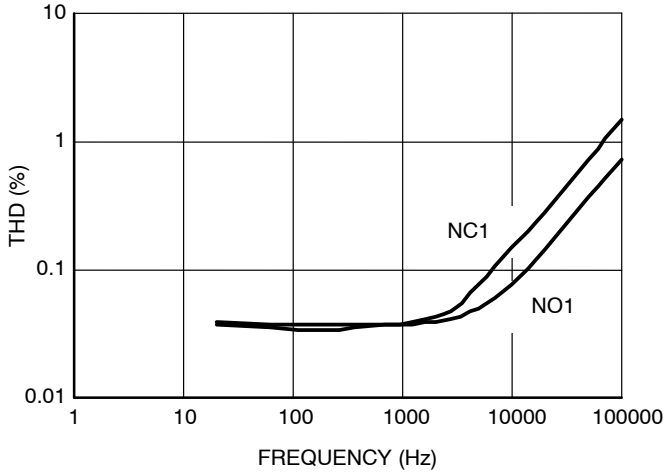


Figure 8. Total Harmonic Distortion Plus Noise Versus Frequency

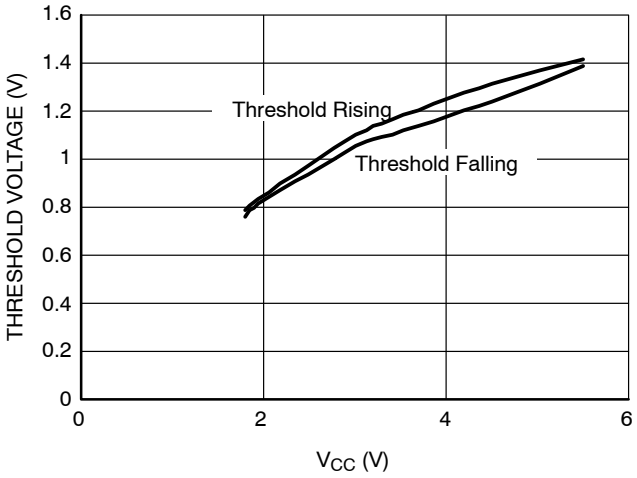


Figure 9. Voltage in Threshold on Logic Pins

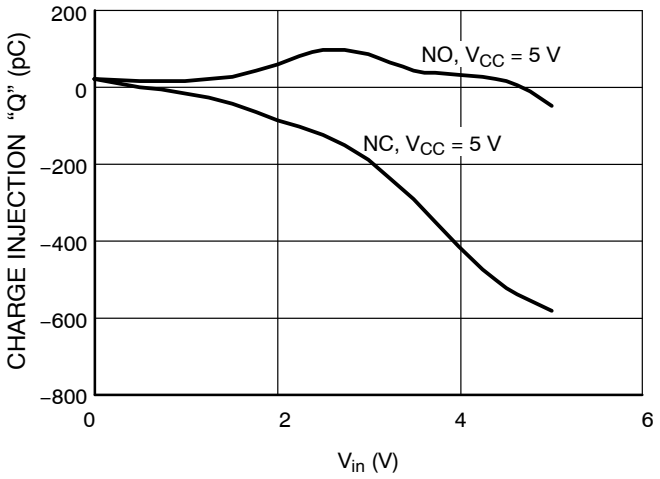


Figure 10. Charge Injection versus V_{is}

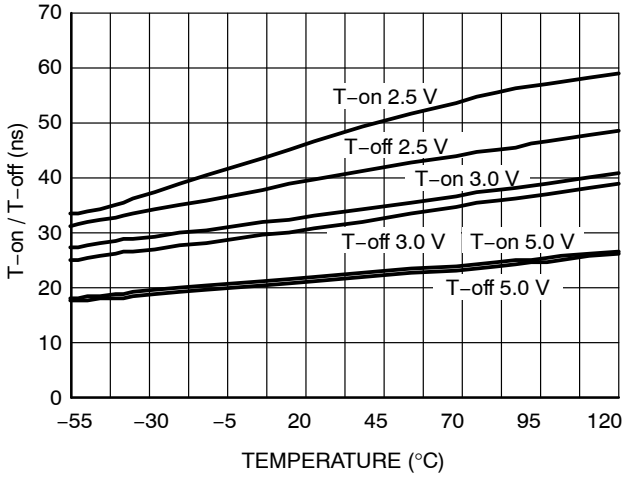


Figure 11. T−on / T−off Time versus Temperature

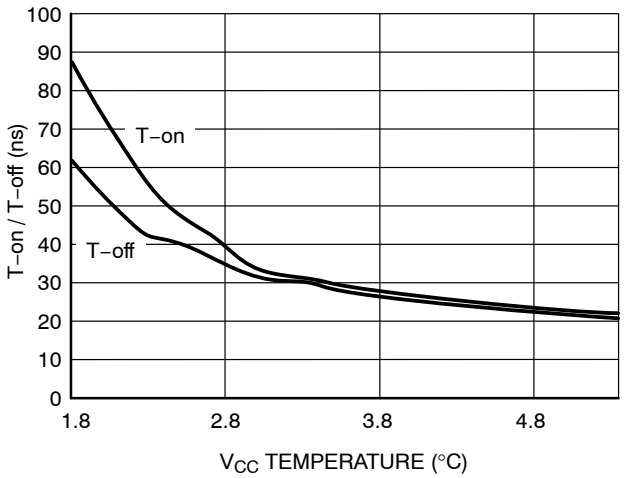


Figure 12. T−on / T−off Time versus Temperature

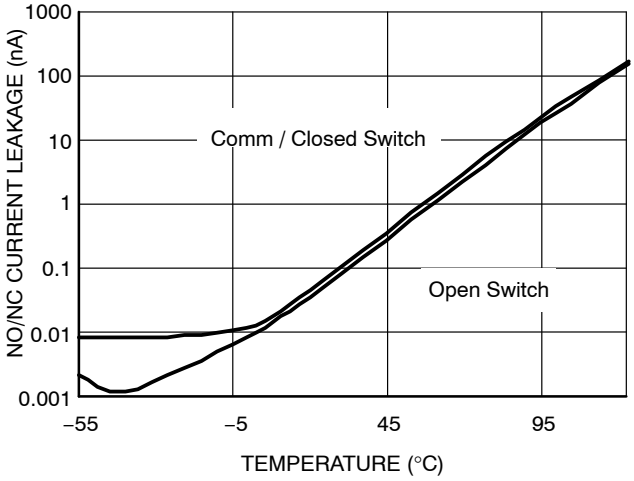


Figure 13. NO/NC Current Leakage Off and On, V_{CC} = 5 V

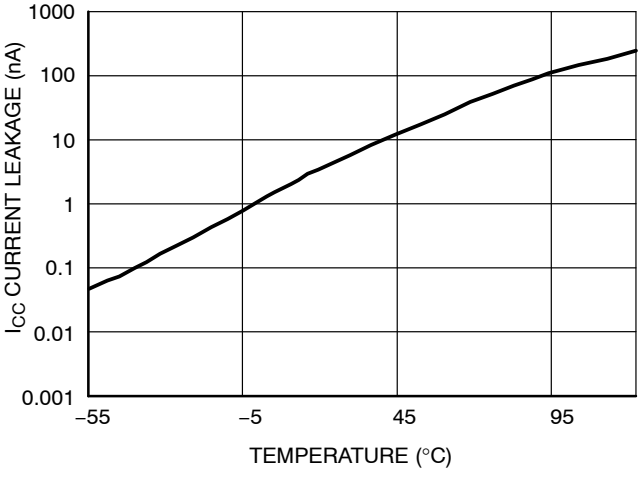


Figure 14. I_{CC} Current Leakage versus Temperature V_{CC} = 5.5 V

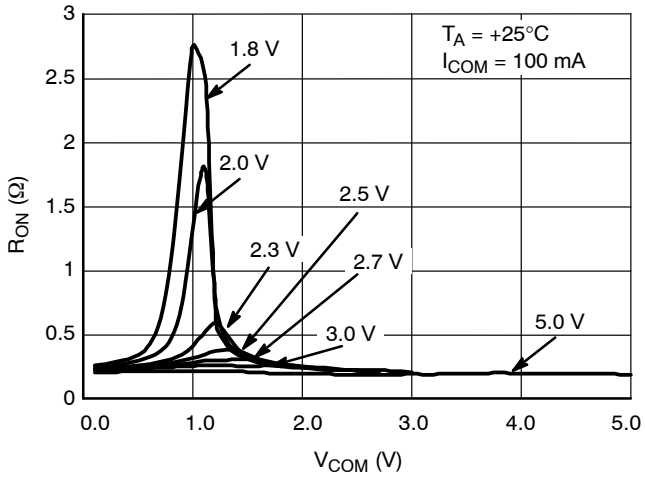


Figure 15. NC On−Resistance versus COM Voltage

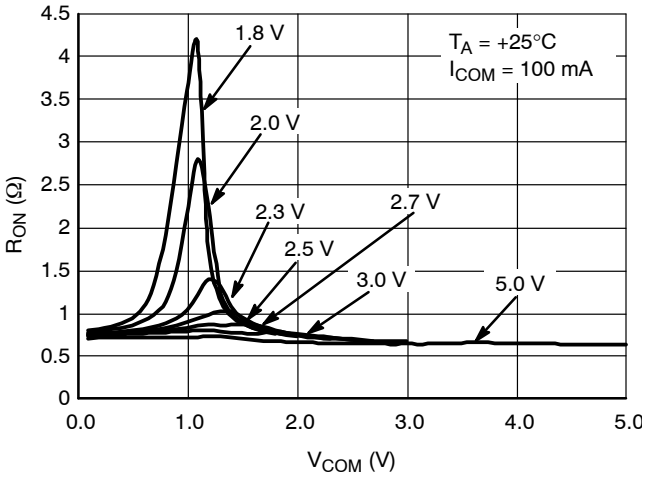


Figure 16. NO On−Resistance versus COM Voltage

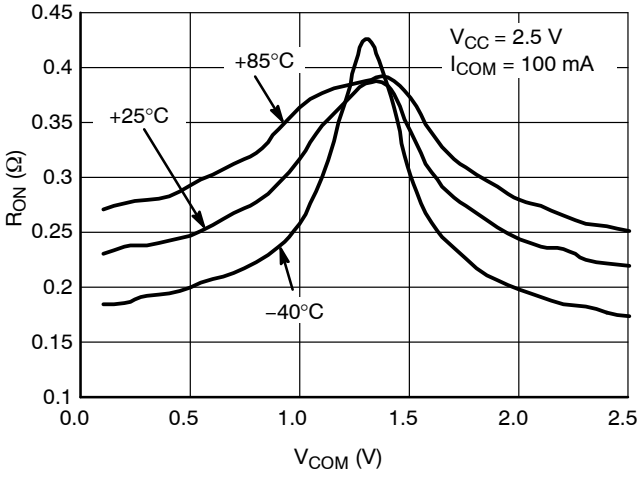


Figure 17. NC On−Resistance versus COM Voltage

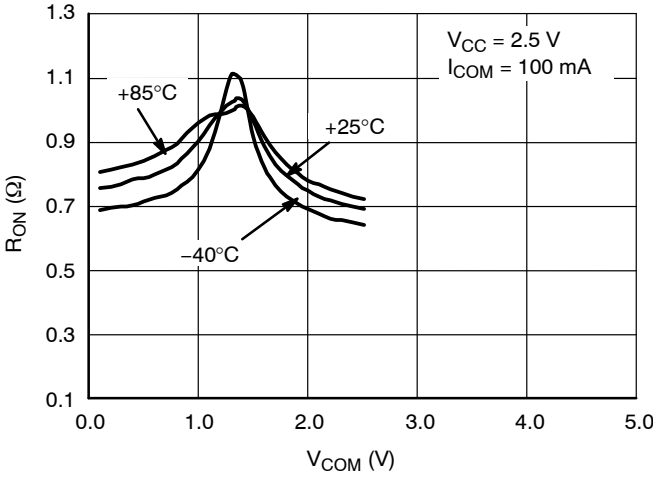


Figure 18. NO On−Resistance versus COM Voltage

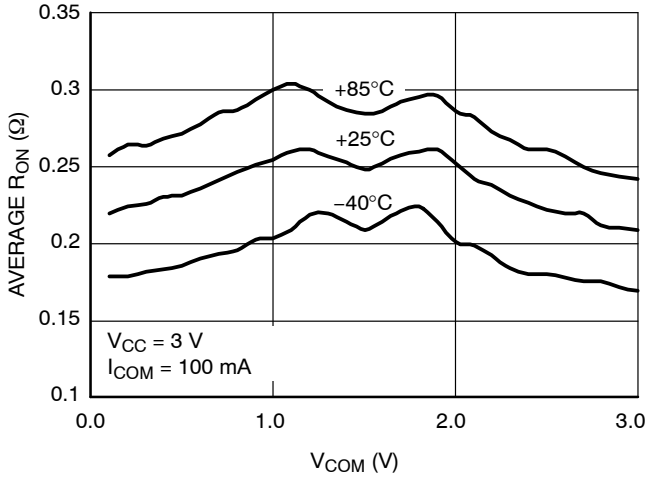


Figure 19. NC On−Resistance versus COM Voltage

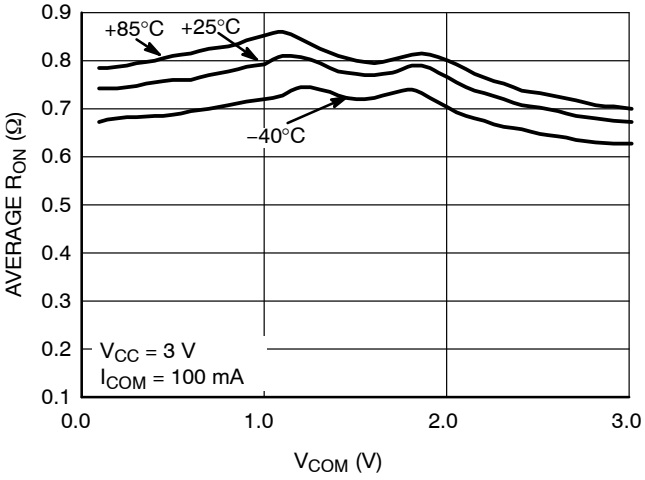


Figure 20. NC On−Resistance versus COM Voltage

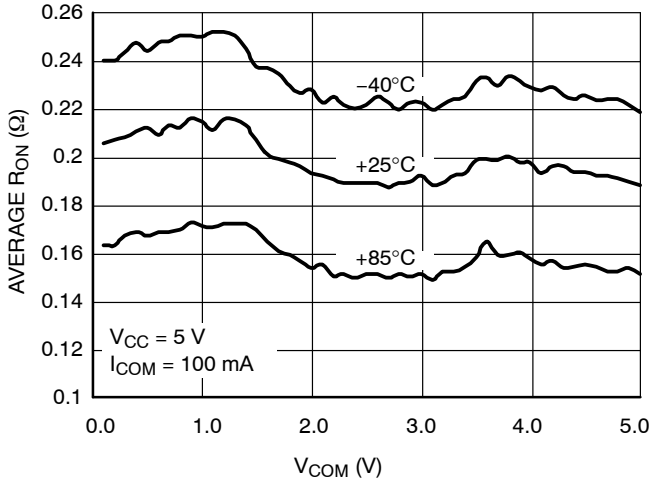


Figure 21. NC On−Resistance versus COM Voltage

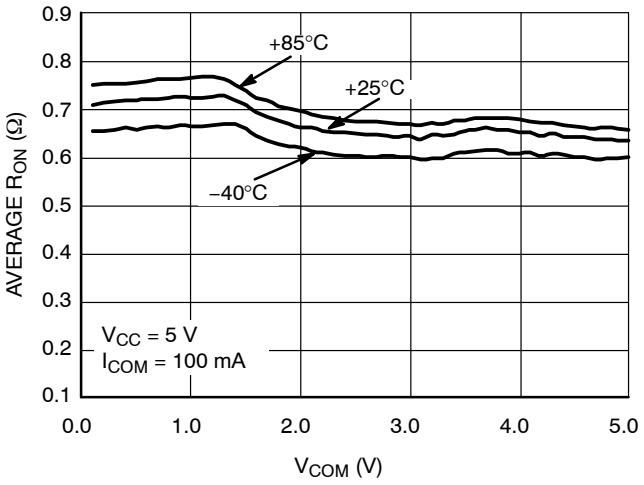


Figure 22. NO On−Resistance versus COM Voltage

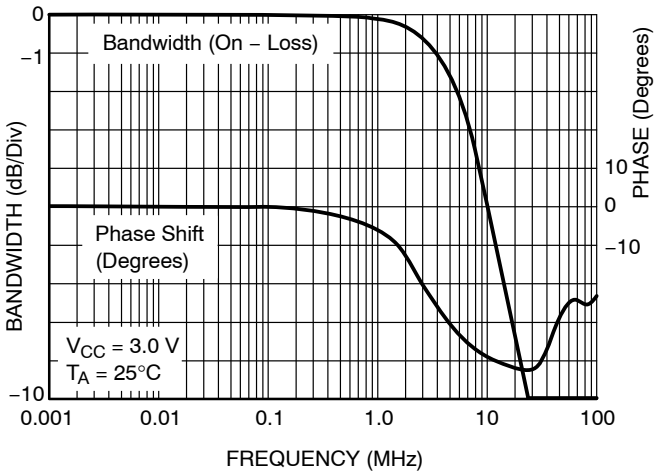


Figure 23. NC Bandwidth and Phase Shift versus Frequency

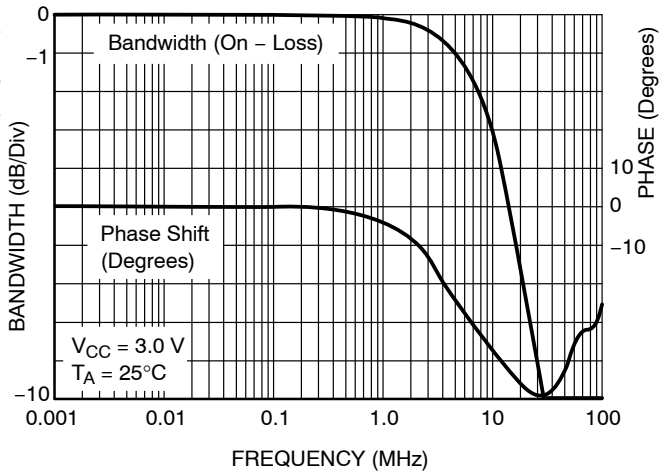


Figure 24. NO Bandwidth and Phase Shift versus Frequency

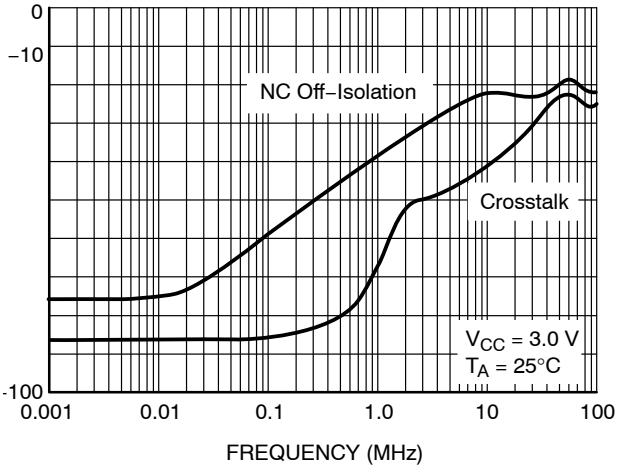


Figure 25. NC Off Isolation and Crosstalk

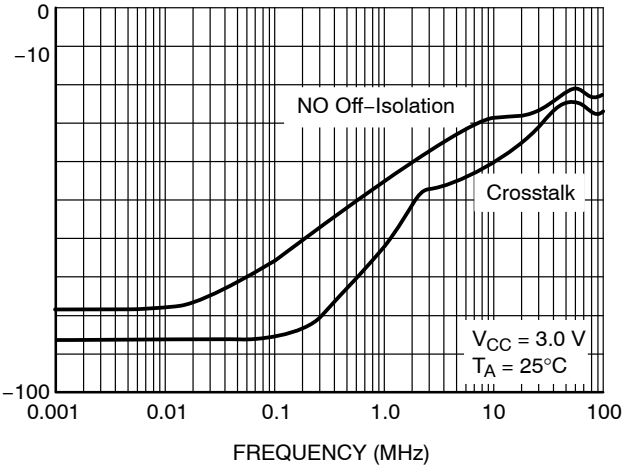


Figure 26. NO Off Isolation and Crosstalk

ORDERING INFORMATION

Device	Package	Shipping†
NLAS4684FCT1	Microbump−10	3000 / Tape & Reel
NLAS4684FCT1G	Microbump−10 (Pb−Free)	3000 / Tape & Reel
NLAS4684FCTCG	Microbump−10 (Pb−Free)	3000 / Tape & Reel
NLAS4684MNR2	DFN10	3000 / Tape & Reel
NLAS4684MNR2G	DFN10 (Pb−Free)	3000 / Tape & Reel
NLAS4684MR2	Micro10	4000 / Tape & Reel
NLAS4684MR2G	Micro10 (Pb−Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

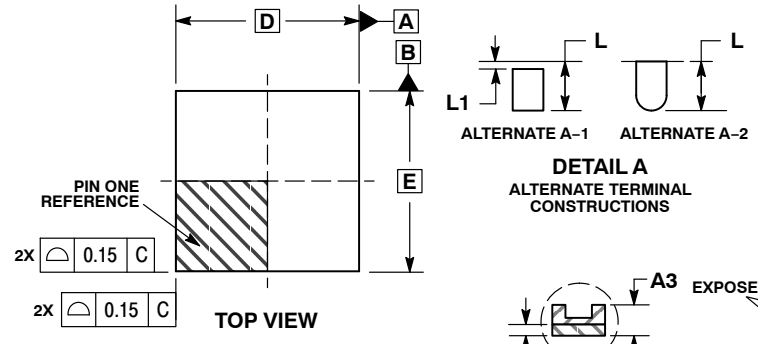
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

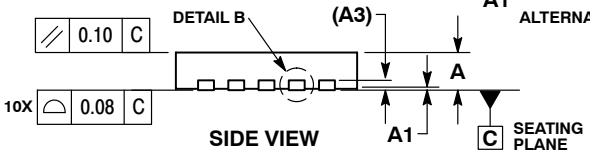
ON Semiconductor®

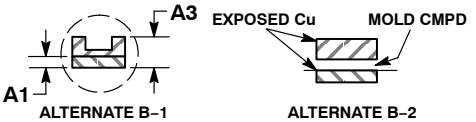
DFN10, 3x3, 0.5P
CASE 485C
ISSUE E

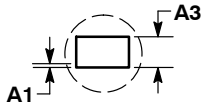
DATE 11 FEB 2016

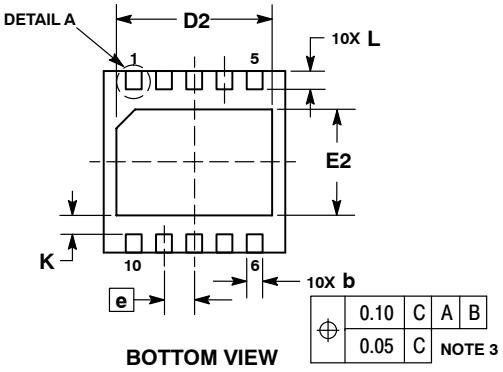
SCALE 2:1











NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. TERMINAL b MAY HAVE MOLD COMPOUND MATERIAL ALONG SIDE EDGE. MOLD FLASHING MAY NOT EXCEED 30 MICRONS ONTO BOTTOM SURFACE OF TERMINAL b.
6. FOR DEVICE OPN CONTAINING W OPTION, DETAIL A AND B ALTERNATE CONSTRUCTION ARE NOT APPLICABLE. WETTABLE FLANK CONSTRUCTION IS DETAIL B AS SHOWN ON SIDE VIEW OF PACKAGE.

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.18	0.30
D	3.00 BSC	
D2	2.40	2.60
E	3.00 BSC	
E2	1.70	1.90
e	0.50 BSC	
K	0.19 TYP	
L	0.35	0.45
L1	0.00	0.03

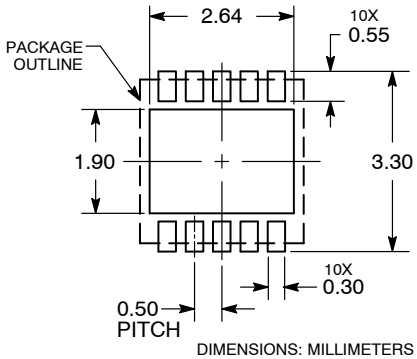
GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

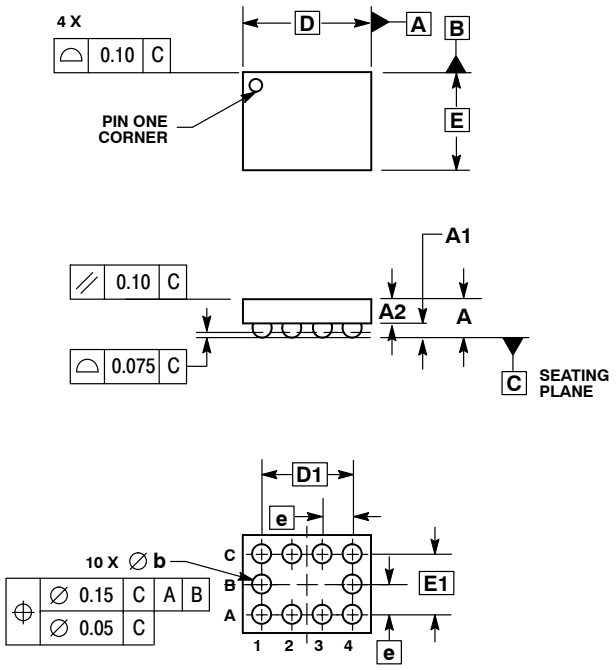
DOCUMENT NUMBER:	**98AON03161D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**DFN10, 3X3 MM, 0.5 MM PITCH**	**PAGE 1 OF 1**

10 PIN FLIP−CHIP
CASE 489AA−01
ISSUE A

DATE 04 MAY 2004

1

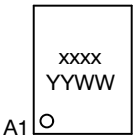
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS	
DIM	MIN	MAX
A	−−−	0.650
A1	0.210	0.270
A2	0.280	0.380
D	1.965 BSC	
E	1.465 BSC	
b	0.250	0.350
e	0.500 BSC	
D1	1.500 BSC	
E1	1.000 BSC	

GENERIC MARKING DIAGRAM*



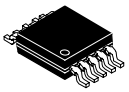
xxxx = Specific Device Code
YY = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

DOCUMENT NUMBER:	**98AON12946D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**10 PIN FLIP−CHIP**		**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

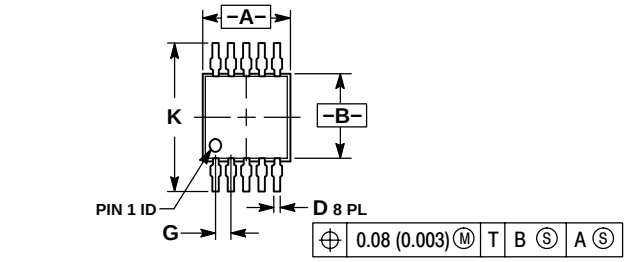
ON Semiconductor®

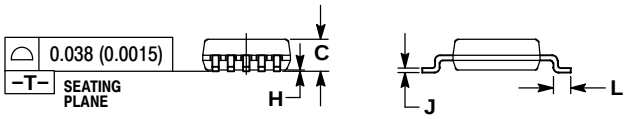


SCALE 2:1

Micro10
CASE 846B−03
ISSUE D

DATE 07 DEC 2004

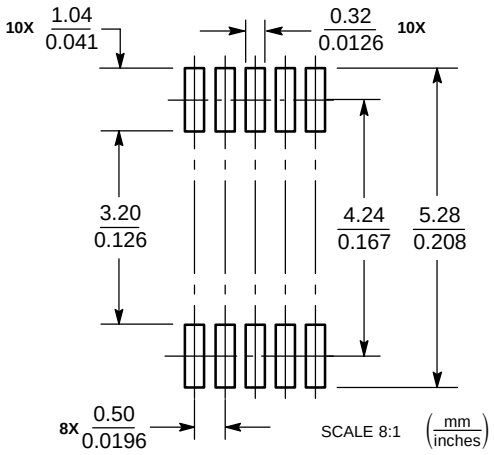




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION “A” DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION “B” DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. 846B−01 OBSOLETE. NEW STANDARD 846B−02

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.95	1.10	0.037	0.043
D	0.20	0.30	0.008	0.012
G	0.50 BSC		0.020 BSC	
H	0.05	0.15	0.002	0.006
J	0.10	0.21	0.004	0.008
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

SOLDERING FOOTPRINT



Micro10

GENERIC MARKING DIAGRAM*

xxxx = Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

DOCUMENT NUMBER:	98AON03799D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
STATUS:	ON SEMICONDUCTOR STANDARD		
NEW STANDARD:			
DESCRIPTION:	Micro10		PAGE 1 OF 2

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION. REQ BY J. HOSKINS.	09 NOV 2000
A	DIM “D” WAS 0.25−0.4MM/0.10−0.016IN. ADDED NOTE 5. USED ON: WAS 10 LEAD TSSOP, PITCH 0.65 REQ BY J. HOSKINS.	13 NOV 2000
B	CHANGED “USED ON” WAS: 10 LEAD TSSOP, PITCH 0.50MM. REQ BY A. HAMID.	11 JUL 2001
C	CHANGED “D” DIMENSION MAX FROM 0.35 TO 0.30MM AND 0.014 TO 0.012IN. REQ BY D. TRUHITTE.	31 JUL 2003
D	ADDED FOOTPRINT INFORMATION. REQ. BY K. OPPEN.	07 DEC 2004

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